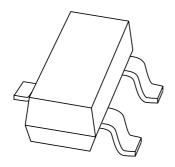
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD6100 High-speed double diode

Product data sheet Supersedes data of 1999 May 11 2003 Mar 25



High-speed double diode

PMBD6100

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- · General application
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

 High-speed switching in surface mounted circuits.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBD6100	*5B

Note

* = p : Made in Hong Kong.
* = t : Made in Malaysia.

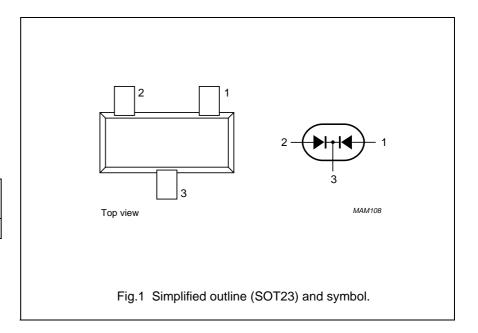
* = W : Made in China.

DESCRIPTION

The PMBD6100 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION			
1	anode (a1)			
2	anode (a2)			
3	common cathode			



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS			
Per diode					
V_{RRM}	repetitive peak reverse voltage		_	85	V
V_R	continuous reverse voltage		_	70	V
l _F	continuous forward current	single diode loaded; note 1; see Fig.2	_	215	mA
		double diode loaded; note 1; see Fig.2	_	125	mA

High-speed double diode

PMBD6100

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{FRM}	repetitive peak forward current		_	450	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode	•	•	•	•	•
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	550	700	mV
		I _F = 10 mA	_	855	mV
		I _F = 50 mA	_	1	V
		I _F = 100 mA	0.85	1.1	V
I_R	reverse current	see Fig.5			
		V _R = 50 V	_	100	nA
		V _R = 50 V; T _j = 150 °C	_	50	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	_	1.5	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	_	4	ns
V _{fr}	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	_	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		360	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

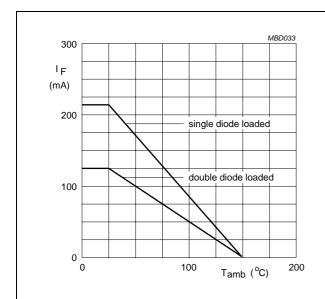
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

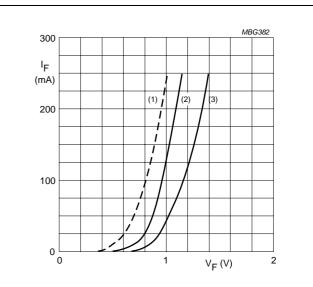
PMBD6100

GRAPHICAL DATA



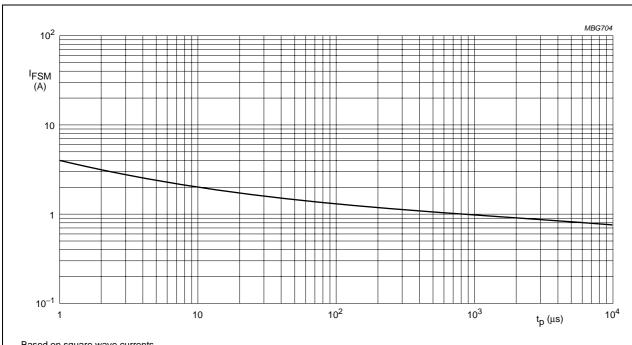
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents. $T_j = 25 \, ^{\circ}\text{C}$ prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

High-speed double diode

PMBD6100

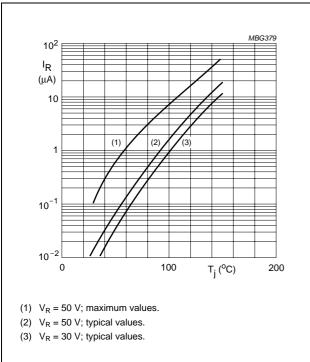


Fig.5 Reverse current as a function of junction

temperature.

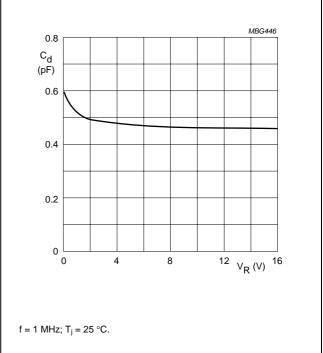
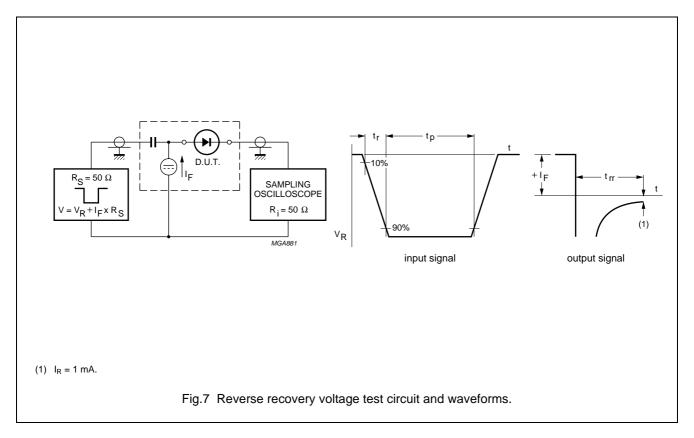
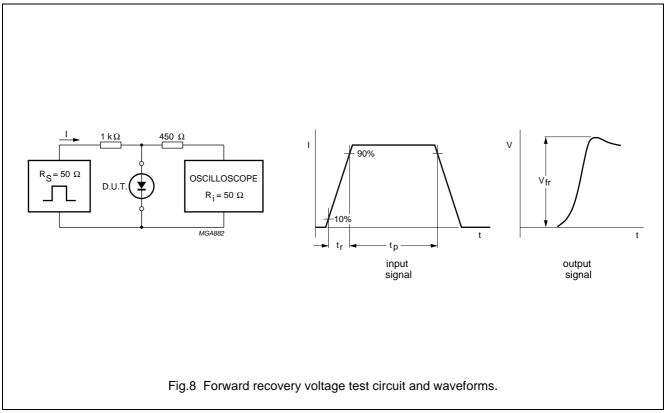


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed double diode

PMBD6100





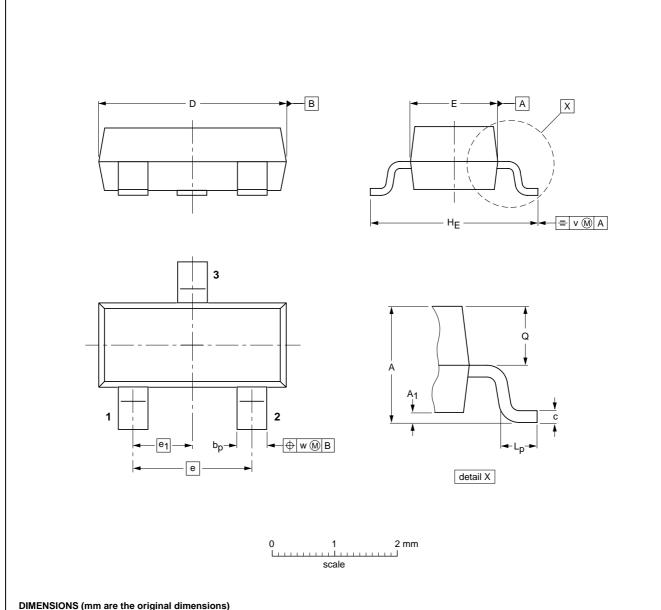
High-speed double diode

PMBD6100

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENS	IONS (m	ım are tı	ne origir	nai dime	nsions)	
						_

UNIT	Α	Max.	bp	С	D	E	е	e ₁	HE	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				97-02-28 99-09-13

High-speed double diode

PMBD6100

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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2003 Mar 25

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

Contact information

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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